TRANSISTOR (PNP)

Plastic-Encapsulate Transistor

FEATURES

Power dissipation

P_{CM} : 500mW (Tamb=25°C)

Collector current

I_{CM} : -800mA

Collector-base Voltage

$V_{(BR)CBO}$: -120 V

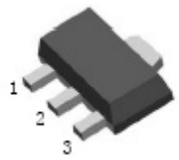
Operating and storage junction temperature range

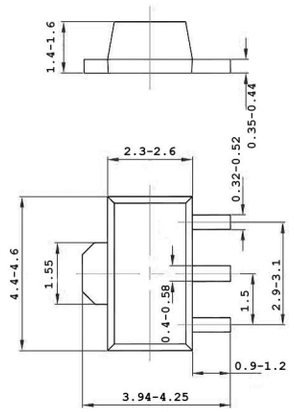
T_J, T_{stg} : -55°C to +150°C

MARKING: DO, DY

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER





UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-1mA, I_E=0	-120			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-120			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-120V, I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC Current Gain	h_{FE}	V_{CE}=-5V, I_C=-100mA	80		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-1	V
Base-Emitter Voltage	V_{BE}	I_C=-500mA, V_{CE}=-5V			-1	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-100mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz			30	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	80-160	120-240

RoHS Pb-free TIP Semiconductor